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May 2012

FDMA7628

Single N-Channel 1.5 V Specified PowerTrench® MOSFET 20 V, 9.4 A, 14.5 m Ω

Features

- Max $r_{DS(on)}$ = 14.5 m Ω at V_{GS} = 4.5 V, I_D = 9.4 A
- Max $r_{DS(on)} = 18.2 \text{ m}\Omega$ at $V_{GS} = 2.5 \text{ V}$, $I_D = 8.3 \text{ A}$
- Max $r_{DS(on)} = 23.3 \text{ m}\Omega$ at $V_{GS} = 1.8 \text{ V}$, $I_D = 7.3 \text{ A}$
- Max $r_{DS(on)} = 32.3 \text{ m}\Omega$ at $V_{GS} = 1.5 \text{ V}$, $I_D = 6.2 \text{ A}$
- Low Profile-0.8 mm maximum in the new package MicroFET 2x2 mm
- RoHS Compliant

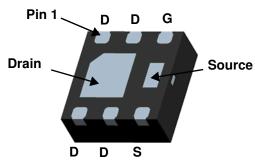


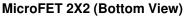
General Description

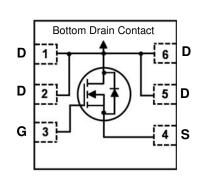
This Single N-Channel MOSFET has been designed using Fairchild Semiconductor's advanced Power Trench® process to optimize the $r_{DS(ON)}$ @ V_{GS} = 1.5 V on special MicroFET leadframe.

Applications

- Li-Ion Battery Pack
- DC-DC Buck Converters







MOSFET Maximum Ratings TA = 25 °C unless otherwise noted

Symbol	Parameter			Ratings	Units
V_{DS}	Drain to Source Voltage			20	V
V_{GS}	Gate to Source Voltage			±8	V
	-Continuous	T _A = 25 °C	(Note 1a)	9.4	Δ.
ID	-Pulsed			54	A
D	Power Dissipation	T _A = 25 °C	(Note 1a)	1.9	14/
P_{D}	Power Dissipation	T _A = 25 °C	(Note 1b)	0.7	W
T _{.I} , T _{STG}	Operating and Storage Junction Tempe	rature Range		-55 to +150	°C

Thermal Characteristics

$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	(Note 1a)	65	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	(Note 1b)	180	-C/VV

Package Marking and Ordering Information

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
104	FDMA7628	MicroFET 2X2	7 "	12 mm	3000 units

Electrical Characteristics $T_J = 25$ °C unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Тур	Max	Units
Off Chara	Off Characteristics					
BV_{DSS}	Drain to Source Breakdown Voltage	$I_D = 250 \mu A, V_{GS} = 0 V$	20			V
$\frac{\Delta BV_{DSS}}{\Delta T_J}$	Breakdown Voltage Temperature Coefficient	I_D = 250 μ A, referenced to 25 °C		15		mV/°C
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} = 16 V, V _{GS} = 0 V			1	μΑ
I _{GSS}	Gate to Source Leakage Current	$V_{GS} = \pm 8 \text{ V}, V_{DS} = 0 \text{ V}$			±100	nA

On Characteristics

$V_{GS(th)}$	Gate to Source Threshold Voltage	$V_{GS} = V_{DS}, I_D = 250 \mu A$	0.4	0.6	1.0	V
$\frac{\Delta V_{GS(th)}}{\Delta T_J}$	Gate to Source Threshold Voltage Temperature Coefficient	I_D = 250 μ A, referenced to 25 °C		-3		mV/°C
		$V_{GS} = 4.5 \text{ V}, I_D = 9.4 \text{ A}$		11.3	14.5	
		$V_{GS} = 2.5 \text{ V}, I_D = 8.3 \text{ A}$		12.7	18.2	
r _{DS(on)}	Static Drain to Source On Resistance	$V_{GS} = 1.8 \text{ V}, I_D = 7.3 \text{ A}$		15.0	23.3	mΩ
	State Brain to course on resistance	$V_{GS} = 1.5 \text{ V}, I_D = 6.2 \text{ A}$		18.3	32.3	11132
		$V_{GS} = 4.5 \text{ V}, I_D = 9.4 \text{ A},$ $T_J = 125 ^{\circ}\text{C}$		14.7	18.3	
9 _{FS}	Forward Transconductance	V _{DD} = 5 V, I _D = 9.4 A		56		S

Dynamic Characteristics

C _{iss}	Input Capacitance	V 10.V.V 0.V	1260	1680	pF
Coss	Output Capacitance	V _{DS} = 10 V, V _{GS} = 0 V, f = 1 MHz	180	240	pF
C _{rss}	Reverse Transfer Capacitance	1 - 1 1011 12	122	185	pF
R_g	Gate Resistance		1.9		Ω

Switching Characteristics

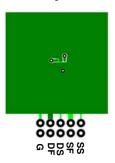
t _{d(on)}	Turn-On Delay Time		9	17	ns
t _r	Rise Time	V _{DD} = 10 V, I _D = 9.4 A,	6	11	ns
t _{d(off)}	Turn-Off Delay Time	V_{GS} = 4.5 V, R_{GEN} = 6 Ω	37	58	ns
t _f	Fall Time		6	11	ns
	Total Gate Charge	V _{GS} = 0 V to 4.5 V	17.5		nC
0	Total Gate Charge	V _{GS} = 0 V to 2.5 V	10.0		nC
Q_g	Total Gate Charge	$V_{GS} = 0 \text{ V to } 1.8 \text{ V} V_{DD} = 10 \text{ V},$	7.4		nC
	Total Gate Charge	V _{GS} = 0 V to 1.5 V I _D = 9.4 A	6.2		nC
Q_{gs}	Gate to Source Charge		1.7		nC
Q_{gd}	Gate to Drain "Miller" Charge		2.7		nC

Drain-Source Diode Characteristics

I _S	Maximum Continuous Drain-Source Diode Forward Current				2.0	Α
V_{SD}	Source to Drain Diode Forward Voltage	$V_{GS} = 0 \text{ V}, I_S = 2.0 \text{ A}$ (Note 2)	0.	63	1.2	V
t _{rr}	Reverse Recovery Time	I _F = 9.4 A, di/dt = 100 A/μs		6	29	ns
Q _{rr}	Reverse Recovery Charge			5	10	nC

NOTES:

1. R_{BJA} is determined with the device mounted on a 1 in² pad 2 oz copper pad on a 1.5 x 1.5 in. board of FR-4 material. R_{BJC} is guaranteed by design while R_{BJA} is determined by the user's board design.



a.65 °C/W when mounted on a 1 in² pad of 2 oz copper.



b. 180 °C/W when mounted on a minimum pad of 2 oz copper.

2. Pulse Test: Pulse Width < 300 μ s, Duty cycle < 2.0%.

Typical Characteristics T_J = 25 °C unless otherwise noted

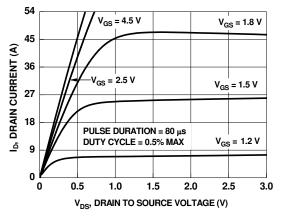


Figure 1. On Region Characteristics

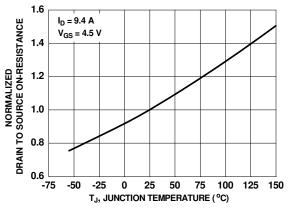


Figure 3. Normalized On Resistance vs Junction Temperature

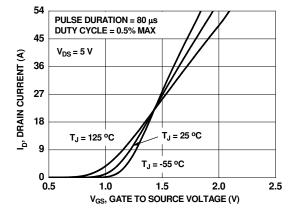


Figure 5. Transfer Characteristics

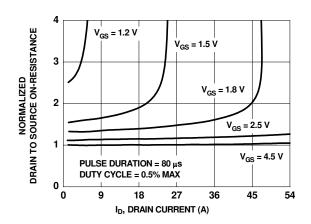


Figure 2. Normalized On-Resistance vs Drain Current and Gate Voltage

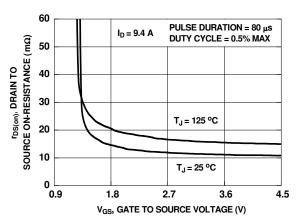


Figure 4. On-Resistance vs Gate to Source Voltage

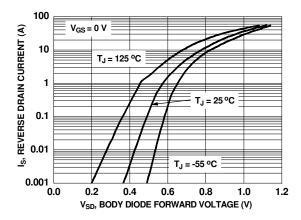


Figure 6. Source to Drain Diode Forward Voltage vs Source Current

Typical Characteristics T_J = 25 °C unless otherwise noted

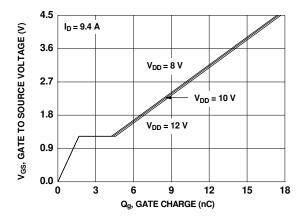


Figure 7. Gate Charge Characteristics

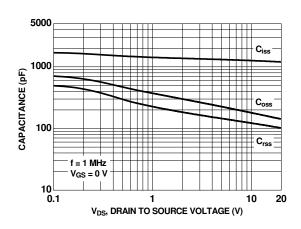


Figure 8. Capacitance vs Drain to Source Voltage

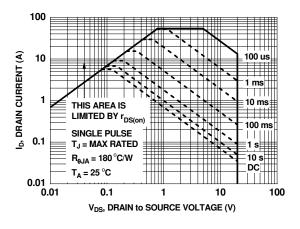


Figure 9. Forward Bias Safe Operating Area

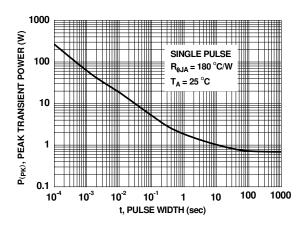


Figure 10. Single Pulse Maximum Power Dissipation

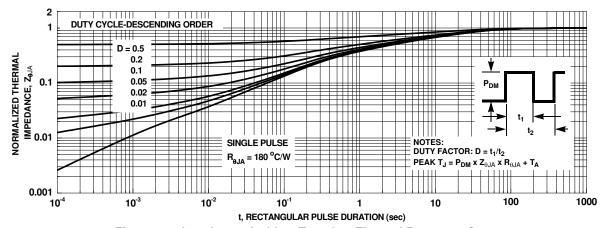
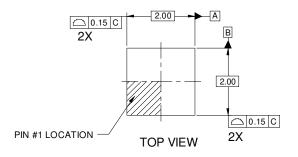
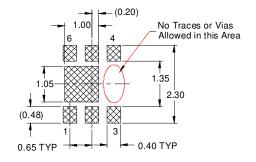


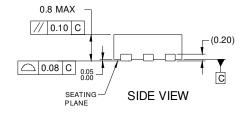
Figure 11. Junction-to-Ambient Transient Thermal Response Curve

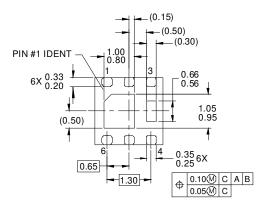
Dimensional Outline and Pad Layout

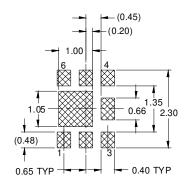




RECOMMENDED LAND PATTERN OPT 1







BOTTOM VIEW

RECOMMENDED LAND PATTERN OPT 2

NOTES:

- A. DOES NOT FULLY CONFORM TO JEDEC REGISTRATION MO-229 DATED AUG/2003
- B. DIMENSIONS ARE IN MILLIMETERS.
- C. DIMENSIONS AND TOLERANCES PER ASME Y14.5M, 1994





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